

# Silicon Carbide Schottky Diode

Product Preview

## FFSM1065B

650 V, 10 A

MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	650	V
Single Pulse Avalanche Energy	$E_{AS}$	TBD	mJ
	$T_J = 25^\circ\text{C}$ , $I_{LPK} = 18\text{ A}$ , $L = 0.5\text{ mH}$ , $V = 50\text{ V}$		
Continuous Rectified Forward Current	$I_F$	$T_C = 124^\circ\text{C}$	10
		$T_C = 135^\circ\text{C}$	8.54
Non-Repetitive Peak Forward Surge Current	$I_{FM}$	$T_C = 25^\circ\text{C}$ , $t_p = 10\ \mu\text{s}$	635
		$T_C = 150^\circ\text{C}$ , $t_p = 10\ \mu\text{s}$	577
Power Dissipation	$P_{tot}$	$T_C = 25^\circ\text{C}$	50.2
		$T_C = 150^\circ\text{C}$	8.37
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Lead Temperature for Soldering Purposes	$T_L$	TBD	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

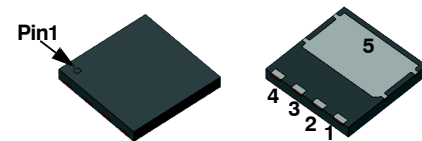
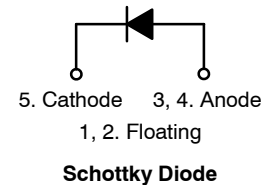
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.99	$^\circ\text{C}/\text{W}$

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



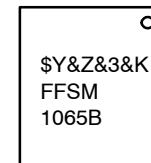
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)



PQFN 8x8, 2P  
CASE 483AP

### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Numeric Date Code  
&K = Lot Code  
FFSM1065B = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSM1065B

## ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

### DIODE CHARACTERISTICS

V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 10 A, T <sub>C</sub> = 25°C	-	1.42	-	V
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 125°C	-	1.57	-	
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 175°C	-	1.72	-	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 650 V, T <sub>C</sub> = 25°C	-	-	40	μA
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 125°C	-	-	80	
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 175°C	-	-	160	

### CHARGES, CAPACITANCES & GATE RESISTANCE

Q <sub>C</sub>	Total Capacitive Charge	V <sub>C</sub> = 600 V	-	31.3	-	nC
C <sub>tot</sub>	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	406	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	45.9	-	
		V <sub>R</sub> = 400 V, f = 100 kHz	-	37.2	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping <sup>†</sup>
FFSM1065B	FFSM1065B	PQFN 8x8, 2P (Halogen Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# FFSM1065B

## TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

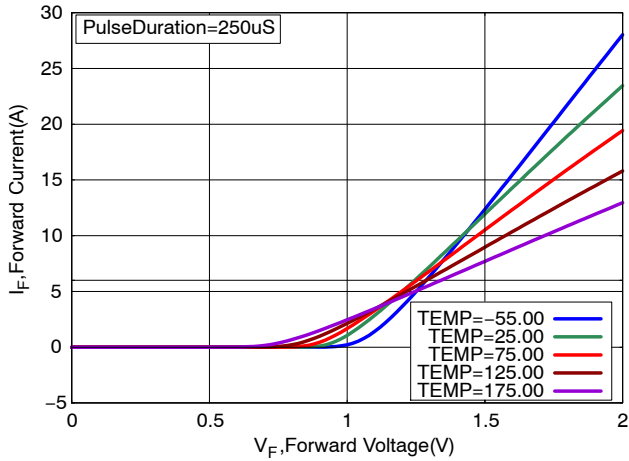


Figure 1. Forward Characteristics

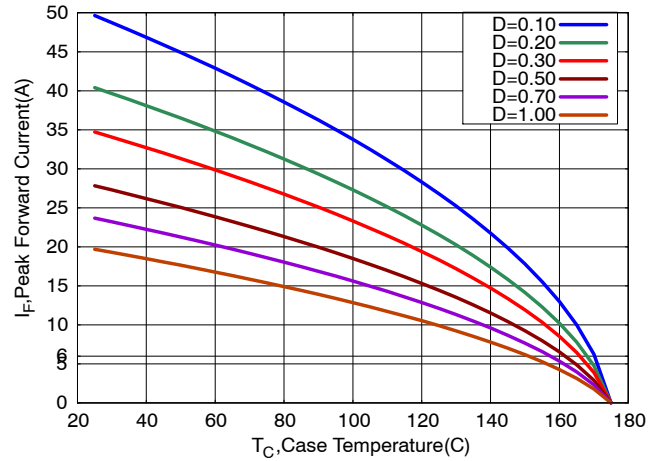


Figure 2. Current Derating

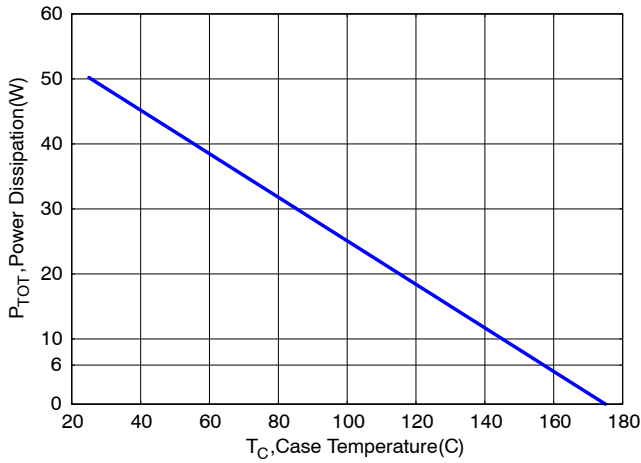


Figure 3. Power Derating

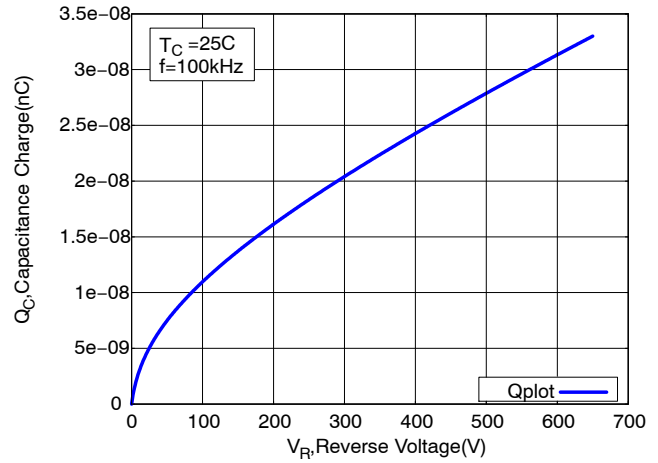


Figure 4. Capacitive Charge vs. Reverse Voltage

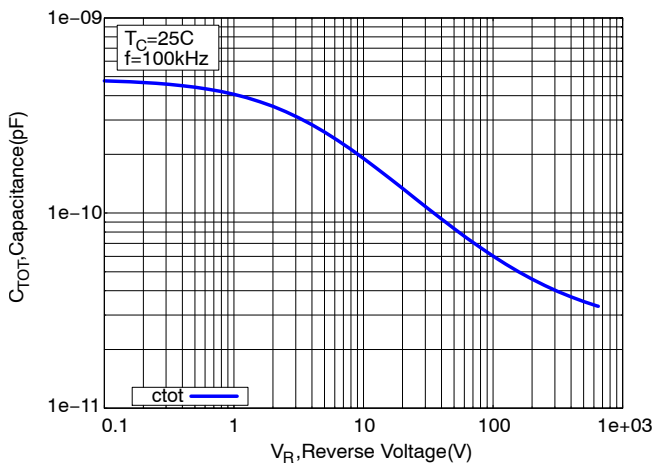


Figure 5. Capacitance vs. Reverse Voltage

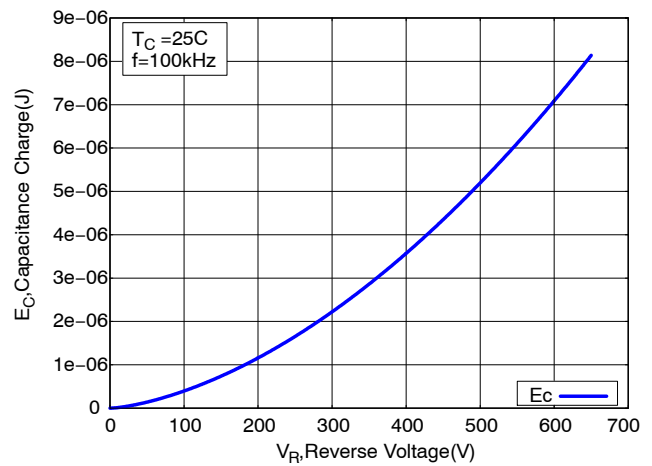


Figure 6. Capacitance Stored Energy

# FFSM1065B

## TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

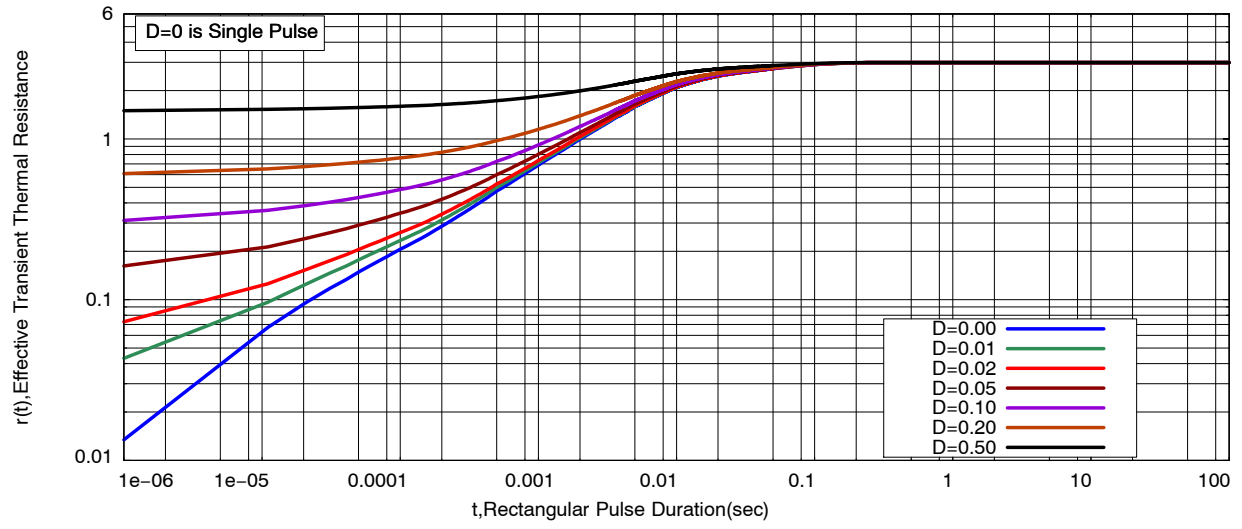
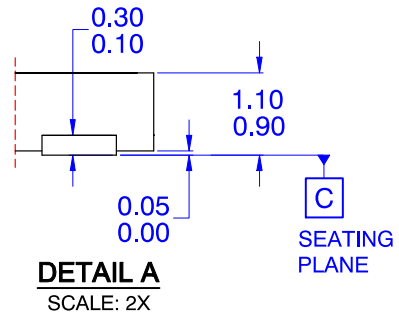
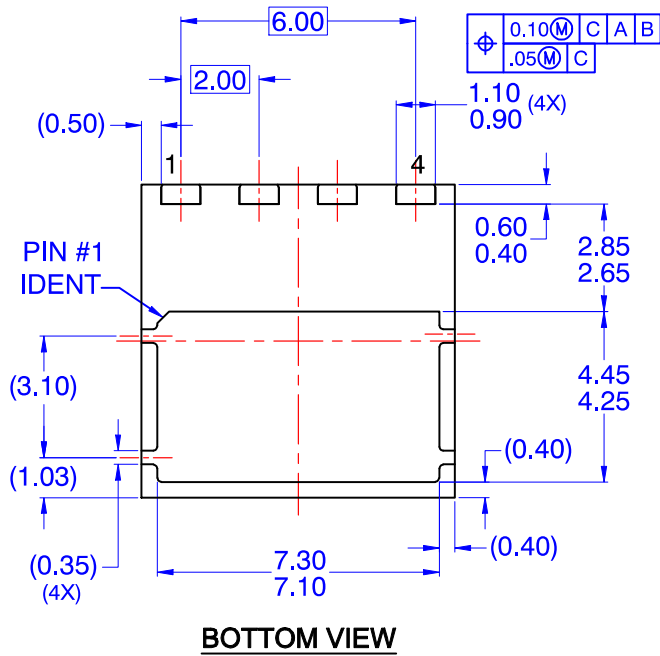
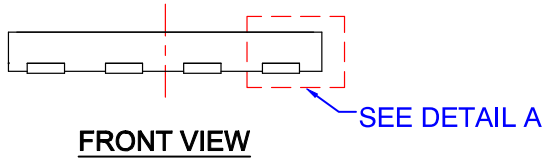
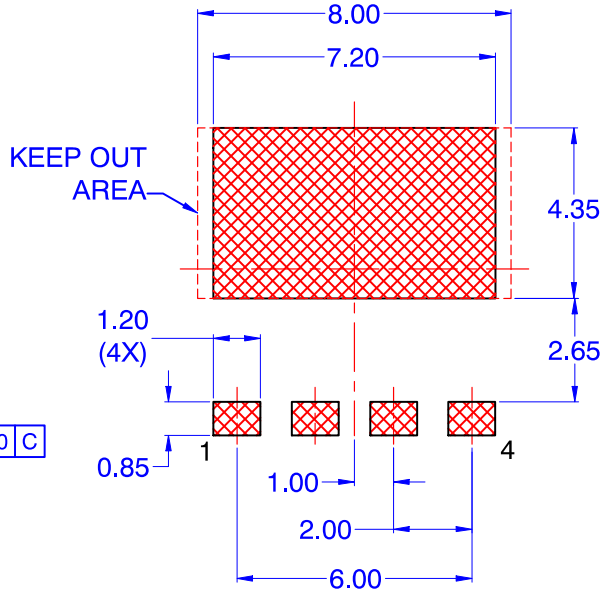
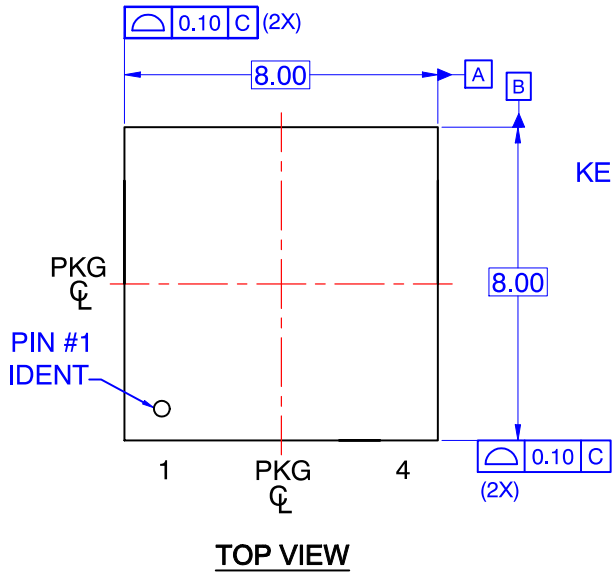


Figure 7. Junction-to-Case Transient Thermal Response


# FFSM1065B

## PACKAGE DIMENSIONS

PQFN4 8X8, 2P  
CASE 483AP  
ISSUE O



NOTES: UNLESS OTHERWISE SPECIFIED  
A) THIS PACKAGE IS NOT PRESENTLY REGISTERED WITH ANY STANDARDS COMMITTEE.  
B) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS.  
C) ALL DIMENSIONS ARE IN MILLIMETERS.  
D) DRAWING CONFORMS TO ASME Y14.5M-1994.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative